

Kevin Lee

List of Publications by Year in Descending Order

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Version: 2024-04-25

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

17
papers

364
citations

10
h-index

17
g-index

17
ext. papers

472
ext. citations

4
avg, IF

3.64
L-index

#	Paper	IF	Citations
17	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 119, 162104	3.4	6
16	MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 118, 092101	3.4	5
15	Enhanced efficiency in bottom tunnel junction InGaIn blue LEDs 2021 ,		3
14	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV $\text{Al}(\text{Ga})\text{O}$ on m-plane sapphire. <i>Science Advances</i> , 2021 , 7,	14.3	35
13	Dislocation and indium droplet related emission inhomogeneities in InGaIn LEDs. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 495106	3	1
12	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. <i>Applied Physics Letters</i> , 2020 , 116, 172106	3.4	17
11	GaN HEMTs on Si With Regrown Contacts and Cutoff/Maximum Oscillation Frequencies of 250/204 GHz. <i>IEEE Electron Device Letters</i> , 2020 , 41, 689-692	4.4	29
10	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2020 , 116, 262102	3.4	17
9	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. <i>Optics Express</i> , 2020 , 28, 4489-4500	3.3	12
8	Bottom tunnel junction blue light-emitting field-effect transistors. <i>Applied Physics Letters</i> , 2020 , 117, 031107	3.4	2
7	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. <i>Applied Physics Letters</i> , 2020 , 117, 061104	3.4	5
6	High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1293-1296	4.4	46
5	Efficient InGaIn p-Contacts for deep-UV Light Emitting Diodes 2019 ,		2
4	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2558-2564	2.9	32
3	Activation of buried p-GaN in MOCVD-regrown vertical structures. <i>Applied Physics Letters</i> , 2018 , 113, 062105	3.4	25
2	MBE-grown 232-270 nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 110, 041108	3.4	85
1	Deep-UV emission at 219 nm from ultrathin MBE GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 111, 091104	3.4	42

